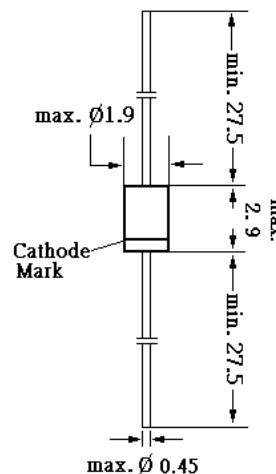


1SS176

SILICON EPITAXIAL PLANAR DIODE

Switching diode



Glass case JEDEC DO-34

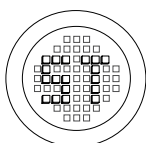
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Peak Reverse Voltage	V_{RM}	35	V
Forward Voltage	I_F	300	mA
Average Rectified Output Current	I_O	100	mA
Surge Forward Current at $t = 1\text{ s}$	I_{FSM}	1000	mA
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_S	-65 to +175	$^\circ\text{C}$

Characteristics at $T_j = 25^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{mA}$	V_F	-	-	1.2	V
Leakage Current at $V_R = 30\text{V}$	I_R	-	-	0.5	μA
Capacitance at $V_R = 0, f = 1\text{MHz}$	C_{tot}	-	-	3	pF
Reverse Recovery Time from $I_F = 100\text{mA}, V_R = 6\text{V}, R_L = 100\Omega$	t_{rr}	-	-	4	ns



®

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